

Silicon PNP Power Transistors

2SB1477

DESCRIPTION

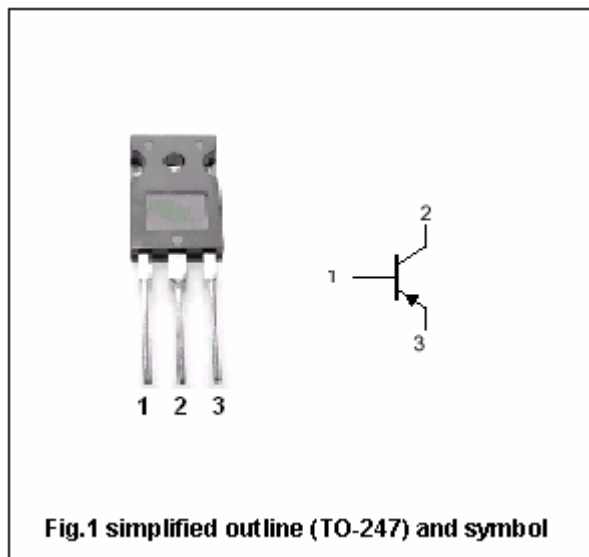
- With TO-247 package
- Complement to type 2SD2236
- Wide area of safe operation

APPLICATIONS

- For driver and general purpose applications

PINNING

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Base                                 |
| 2   | Collector;connected to mounting base |
| 3   | Emitter                              |



Absolute maximum ratings(Tc=25°C)

| SYMBOL           | PARAMETER                   | CONDITIONS           | VALUE   | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V <sub>CBO</sub> | Collector-base voltage      | Open emitter         | -100    | V    |
| V <sub>CEO</sub> | Collector-emitter voltage   | Open base            | -100    | V    |
| V <sub>EBO</sub> | Emitter-base voltage        | Open collector       | -5      | V    |
| I <sub>C</sub>   | Collector current           |                      | -5      | A    |
| P <sub>C</sub>   | Collector power dissipation | T <sub>C</sub> =25°C | 60      | W    |
| T <sub>j</sub>   | Junction temperature        |                      | 150     | °C   |
| T <sub>stg</sub> | Storage temperature         |                      | -55~150 | °C   |

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                  | MIN  | TYP. | MAX  | UNIT |
|----------------------|--------------------------------------|---|------|------|------|------|
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =-10mA; I <sub>B</sub> =0    | -100 |      |      | V    |
| V <sub>(BR)CBO</sub> | Collector-base breakdown voltage     | I <sub>C</sub> =-0.1mA; I <sub>E</sub> =0   | -100 |      |      | V    |
| V <sub>(BR)EBO</sub> | Emitter-base breakdown voltage       | I <sub>E</sub> =-0.1mA; I <sub>C</sub> =0   | -5   |      |      | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3 A |      |      | -1.5 | V    |
| V <sub>BEsat</sub>   | Base-emitter saturation voltage      | I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3 A |      |      | -2.0 | V    |
| I <sub>CBO</sub>     | Collector cut-off current            | V <sub>CB</sub> =-100V; I <sub>E</sub> =0   |      |      | -10  | μA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =-5V; I <sub>C</sub> =0     |      |      | -10  | μA   |
| h <sub>FE</sub>      | DC current gain                      | I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V  | 60   |      | 320  |      |

◆ h<sub>FE</sub> classifications

| D      | E       | F       |
|--------|---------|---------|
| 60-120 | 100-200 | 160-320 |

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PACKAGE OUTLINE

